

**VHF/UHF NPN Epitaxial Planar Transistor**

# BTNH10N3

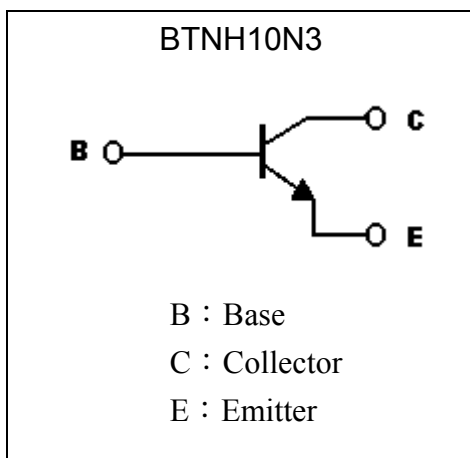
## Description

The BTNH10N3 is designed for use in VHF & UHF oscillators and VHF mixer in tuner of a TV receiver.

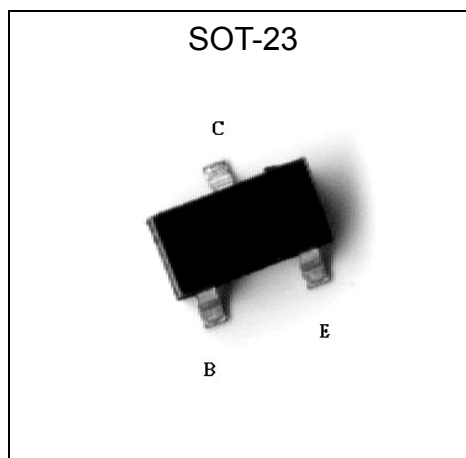
## Features

- High transition frequency.
- Very low capacitance.
- Small  $R_{bb'}$ - $C_c$  and high current gain.
- Pb-free package

## Symbol



## Outline



## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	3	V
Collector Current	$I_C$	50	mA
Power Dissipation	$P_d$	225	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C



**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	30	-	-	V	I <sub>C</sub> =100μA
BV <sub>CEO</sub>	25	-	-	V	I <sub>C</sub> =1mA
BV <sub>EBO</sub>	3	-	-	V	I <sub>C</sub> =10μA
I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> =25V
I <sub>EBO</sub>	-	-	100	nA	V <sub>EB</sub> =2V
*V <sub>CE(sat)</sub>	-	-	0.5	V	I <sub>C</sub> =4mA, I <sub>B</sub> =0.4mA
*V <sub>BE(on)</sub>	-	-	0.95	V	V <sub>CE</sub> =10V, I <sub>C</sub> =4mA
*h <sub>FE</sub>	52	-	270	-	V <sub>CE</sub> =10V, I <sub>C</sub> =4mA
f <sub>T</sub>	650	1000	-	MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =4mA, f=100MHz
C <sub>ob</sub>	-	-	0.7	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz
R <sub>bb'</sub> -C <sub>c</sub>	-	-	9	ps	V <sub>CB</sub> =10V, I <sub>C</sub> =4mA, f=31.8MHz

\*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of h<sub>FE</sub>**

Rank	K	P	Q
Range	52~120	82~180	120~270

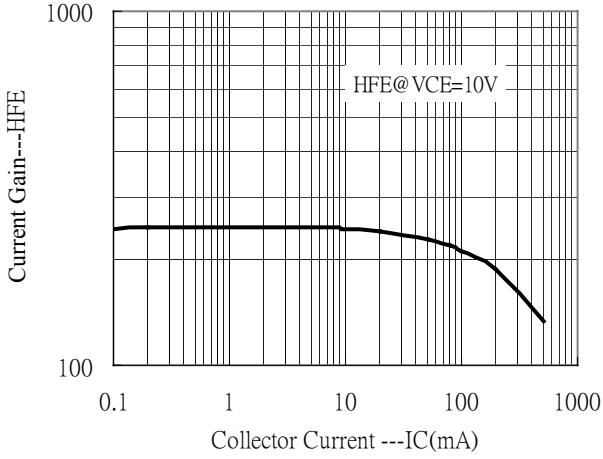
**Ordering Information**

Device	Package	Shipping	Marking
BTNH10N3	SOT-23 (Pb-free)	3000 pcs / Tape & Reel	3E

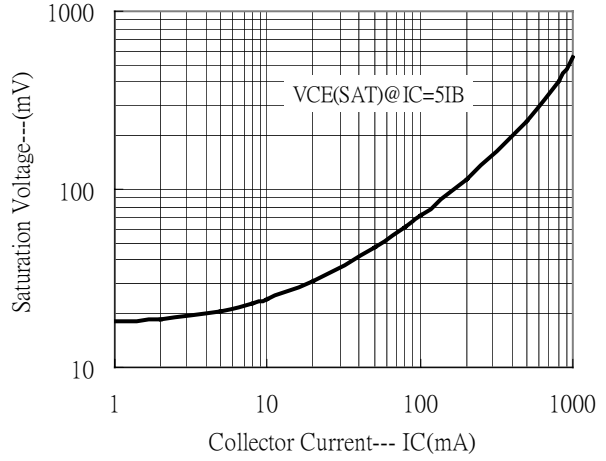


### Characteristic Curves

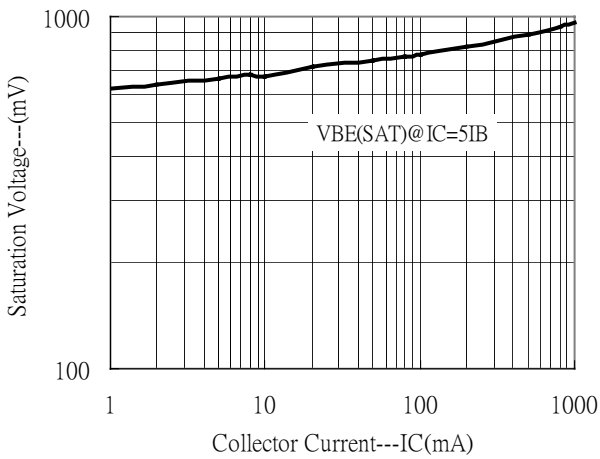
Current Gain vs Collector Current



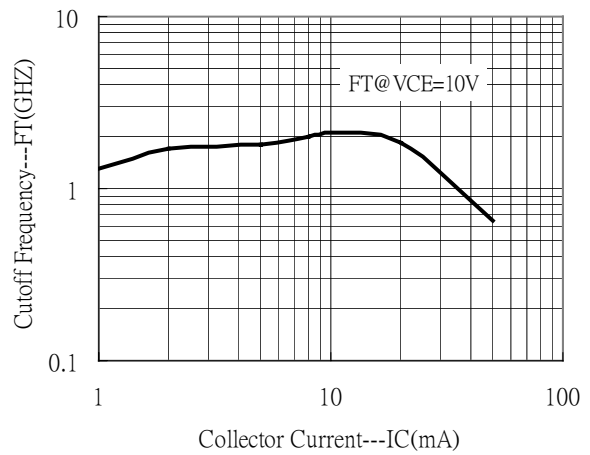
Saturation Voltage vs Collector Current



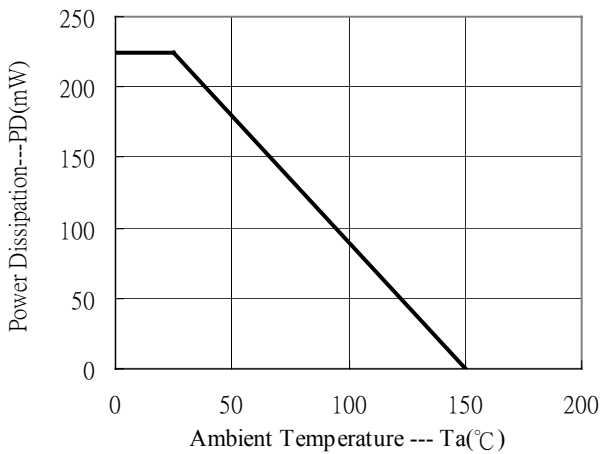
Saturation Voltage vs Collector Current



Cutoff Frequency vs Collector Current

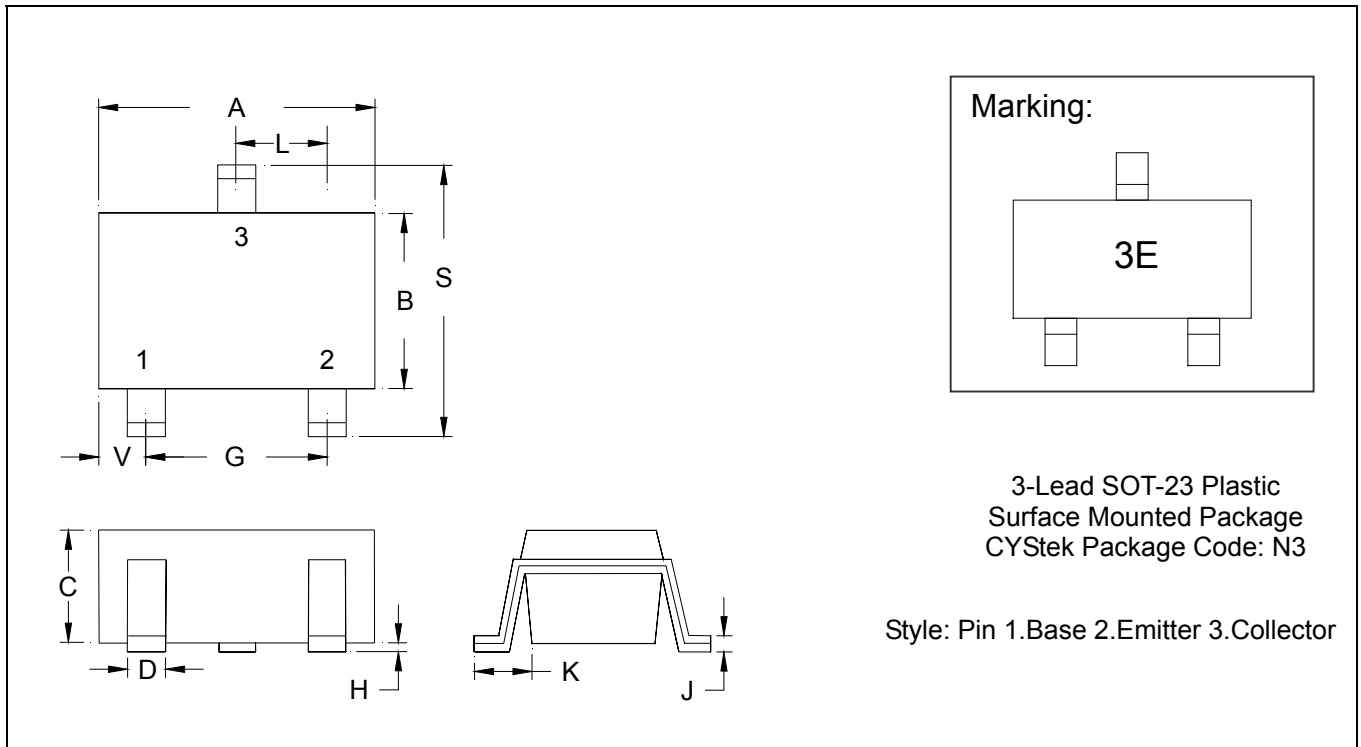


Power Derating Curve





**SOT-23 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

- Notes:** 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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